

# DMG204B1

Silicon NPN epitaxial planar type (Tr1)  
Silicon PNP epitaxial planar type (Tr2)

For low frequency amplification

■ Features

- High forward current transfer ratio  $h_{FE}$  with excellent linearity
- Low collector-emitter saturation voltage  $V_{CE(sat)}$
- Halogen-free / RoHS compliant  
(EU RoHS / UL-94 V-0 / MSL: Level 1 compliant)

■ Marking Symbol: C5

■ Basic Part Number

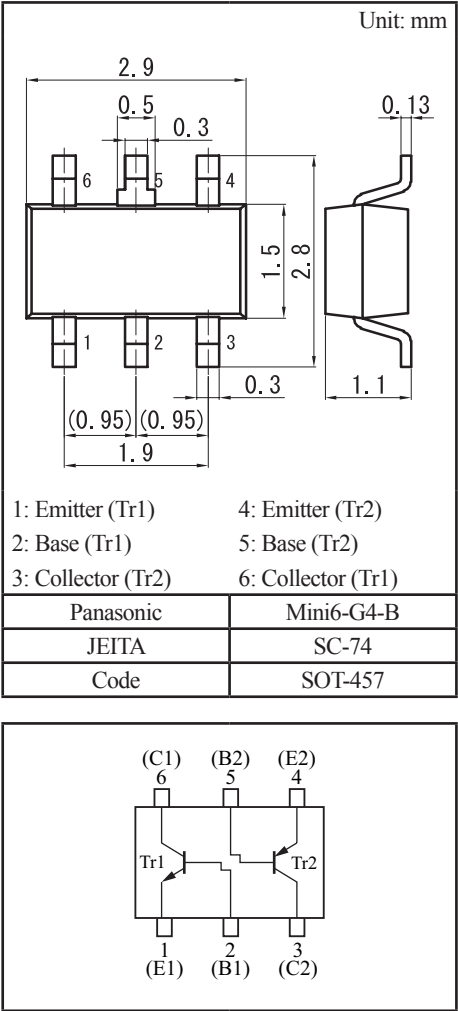
DSC2501 + DSA2001 (Individual)

■ Packaging

DMG204B10R Embossed type (Thermo-compression sealing): 3 000 pcs / reel (standard)

■ Absolute Maximum Ratings  $T_a = 25^{\circ}\text{C}$

Parameter		Symbol	Rating	Unit
Tr1	Collector-base voltage (Emitter open)	$V_{CBO}$	25	V
	Collector-emitter voltage (Base open)	$V_{CEO}$	20	V
	Emitter-base voltage (Collector open)	$V_{EBO}$	12	V
	Collector current	$I_C$	0.5	A
	Peak collector current	$I_{CP}$	1	A
Tr2	Collector-base voltage (Emitter open)	$V_{CBO}$	-60	V
	Collector-emitter voltage (Base open)	$V_{CEO}$	-50	V
	Emitter-base voltage (Collector open)	$V_{EBO}$	-7	V
	Collector current	$I_C$	-100	mA
	Peak collector current	$I_{CP}$	-200	mA
Overall	Total power dissipation	$P_T$	300	mW
	Junction temperature	$T_j$	150	$^{\circ}\text{C}$
	Operating ambient temperature	$T_{opr}$	-40 to +85	$^{\circ}\text{C}$
	Storage temperature	$T_{stg}$	-55 to +150	$^{\circ}\text{C}$



■ Electrical Characteristics  $T_a = 25^\circ\text{C} \pm 3^\circ\text{C}$

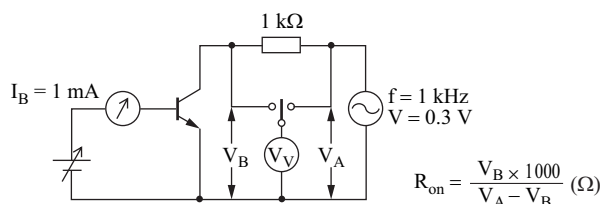
• Tr1

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Collector-base voltage (Emitter open)	$V_{\text{CBO}}$	$I_{\text{C}} = 10 \mu\text{A}, I_{\text{E}} = 0$	25			V
Collector-emitter voltage (Base open)	$V_{\text{CEO}}$	$I_{\text{C}} = 1 \text{ mA}, I_{\text{B}} = 0$	20			V
Emitter-base voltage (Collector open)	$V_{\text{EBO}}$	$I_{\text{E}} = 10 \mu\text{A}, I_{\text{C}} = 0$	12			V
Collector-base cutoff current (Emitter open)	$I_{\text{CBO}}$	$V_{\text{CB}} = 25 \text{ V}, I_{\text{E}} = 0$			100	nA
Forward current transfer ratio	$h_{\text{FE}}$	$V_{\text{CE}} = 2 \text{ V}, I_{\text{C}} = 0.5 \text{ A}$	200		800	—
Collector-emitter saturation voltage <sup>*1</sup>	$V_{\text{CE(sat)}}$	$I_{\text{C}} = 0.5 \text{ A}, I_{\text{B}} = 20 \text{ mA}$		0.18	0.40	V
Base-emitter saturation voltage <sup>*1</sup>	$V_{\text{BE(sat)}}$	$I_{\text{C}} = 0.5 \text{ A}, I_{\text{B}} = 50 \text{ mA}$			1.2	V
Transition frequency	$f_{\text{T}}$	$V_{\text{CE}} = 10 \text{ V}, I_{\text{C}} = 50 \text{ mA}$		150		MHz
Collector output capacitance (Common base, input open circuited)	$C_{\text{ob}}$	$V_{\text{CB}} = 10 \text{ V}, I_{\text{E}} = 0, f = 1 \text{ MHz}$		6		pF
ON resistance <sup>*2</sup>	$R_{\text{on}}$			1.0		$\Omega$

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

2. \*1: Pulse measurement

\*2: Ron measurement circuit

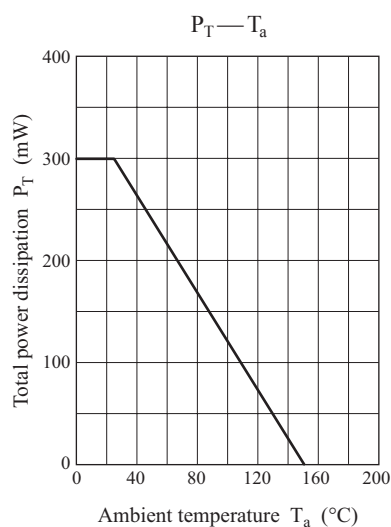


• Tr2

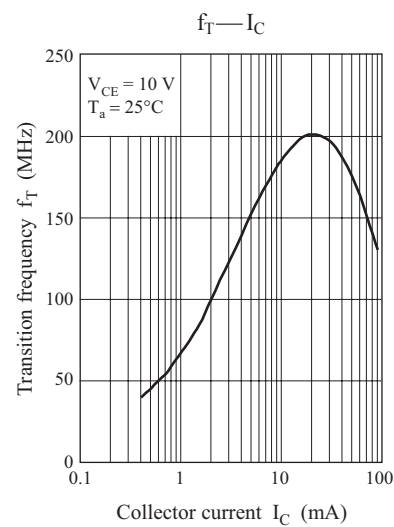
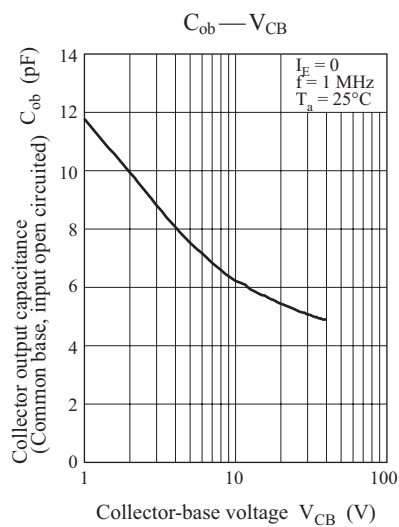
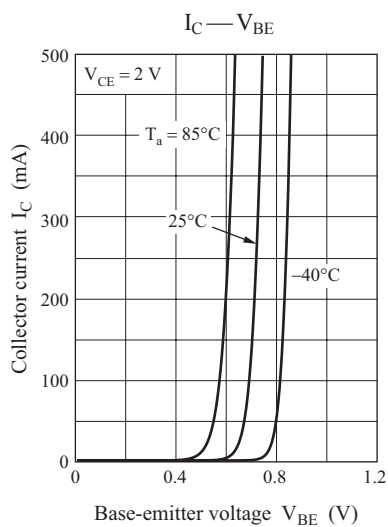
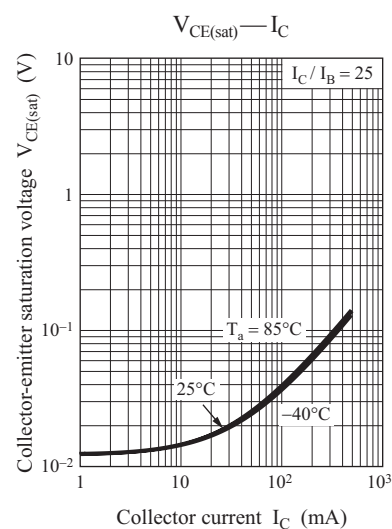
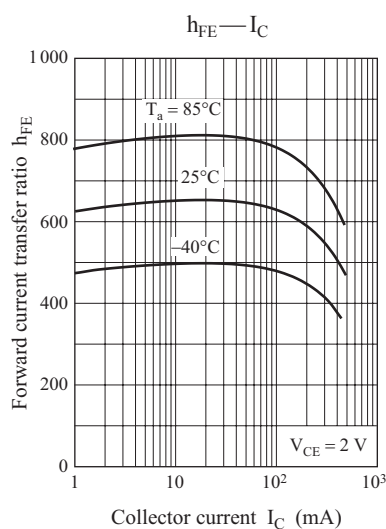
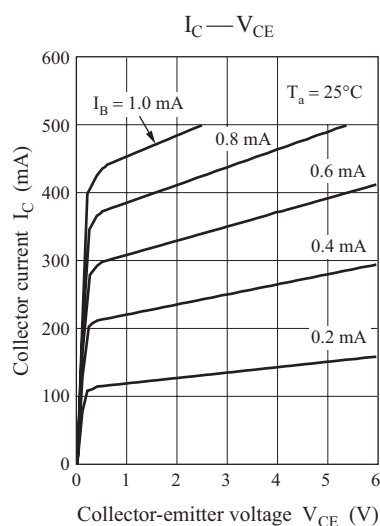
Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Collector-base voltage (Emitter open)	$V_{\text{CBO}}$	$I_{\text{C}} = -10 \mu\text{A}, I_{\text{E}} = 0$	-60			V
Collector-emitter voltage (Base open)	$V_{\text{CEO}}$	$I_{\text{C}} = -2 \text{ mA}, I_{\text{B}} = 0$	-50			V
Emitter-base voltage (Collector open)	$V_{\text{EBO}}$	$I_{\text{E}} = -10 \mu\text{A}, I_{\text{C}} = 0$	-7			V
Collector-base cutoff current (Emitter open)	$I_{\text{CBO}}$	$V_{\text{CB}} = -20 \text{ V}, I_{\text{E}} = 0$			-0.1	$\mu\text{A}$
Collector-emitter cutoff current (Base open)	$I_{\text{CEO}}$	$V_{\text{CE}} = -10 \text{ V}, I_{\text{B}} = 0$			-100	$\mu\text{A}$
Forward current transfer ratio	$h_{\text{FE}}$	$V_{\text{CE}} = -10 \text{ V}, I_{\text{C}} = -2 \text{ mA}$	210		460	—
Collector-emitter saturation voltage	$V_{\text{CE(sat)}}$	$I_{\text{C}} = -100 \text{ mA}, I_{\text{B}} = -10 \text{ mA}$		-0.2	-0.5	V
Transition frequency	$f_{\text{T}}$	$V_{\text{CE}} = -10 \text{ V}, I_{\text{C}} = -2 \text{ mA}$		150		MHz
Collector output capacitance (Common base, input open circuited)	$C_{\text{ob}}$	$V_{\text{CB}} = -10 \text{ V}, I_{\text{E}} = 0, f = 1 \text{ MHz}$		2		pF

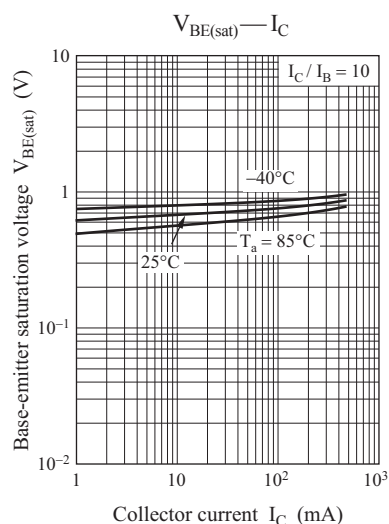
Note) Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

Common characteristics chart

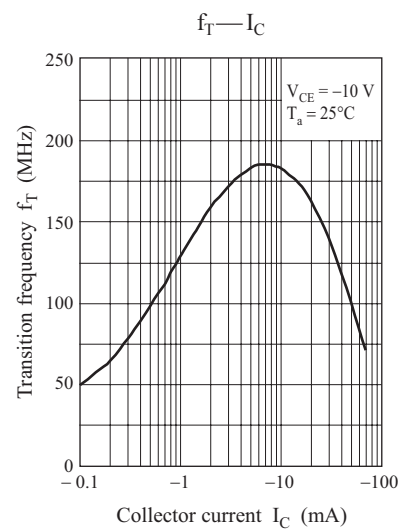
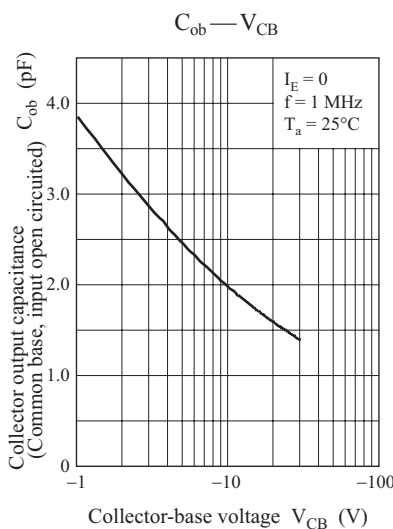
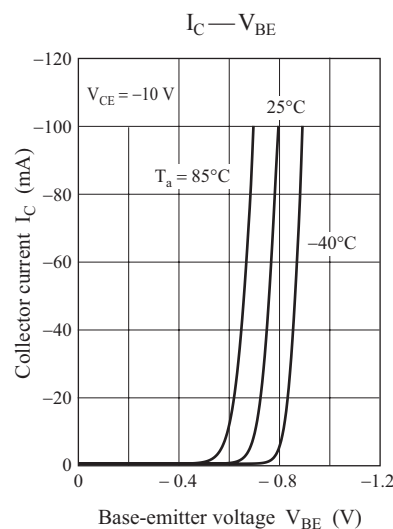
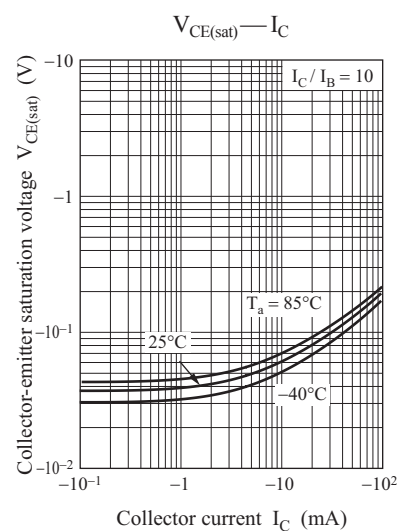
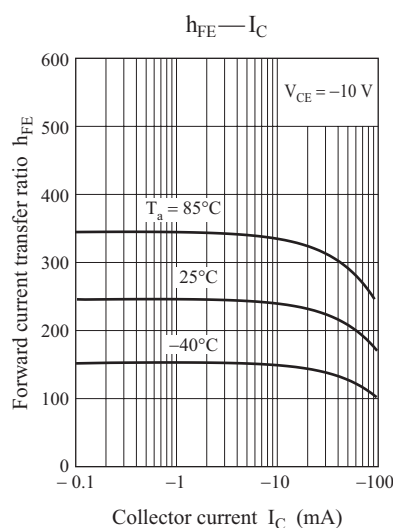
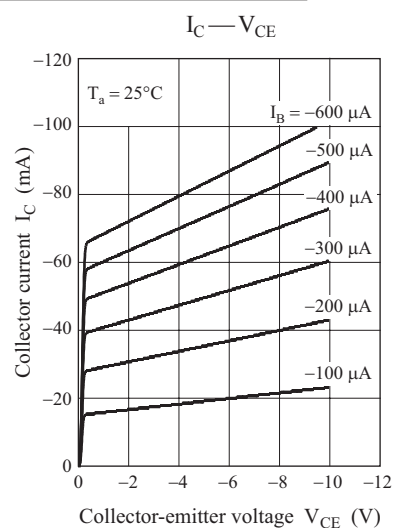


Characteristics charts of Tr1





### Characteristics charts of Tr2





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